

Varra Rajagopal Reddy

List of Publications by Year in descending order

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171
papers

2,897
citations

186209

28
h-index

276775

41
g-index

173
all docs

173
docs citations

173
times ranked

1801
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical properties of Au/polyvinylidene fluoride/n-InP Schottky diode with polymer interlayer. Thin Solid Films, 2014, 556, 300-306.	0.8	119
2	Electrical Properties and Current Transport Mechanisms of the Au/n-GaN Schottky Structure with Solution- Processed High-k BaTiO ₃ Interlayer. Journal of Electronic Materials, 2014, 43, 3499-3507.	1.0	80
3	Electrical characterization of Au/n-GaN metal-insulator-semiconductor and Au/SiO ₂ /n-GaN metal-insulator-semiconductor structures. Journal of Alloys and Compounds, 2011, 509, 8001-8007.	2.8	75
4	Study of current-voltage-temperature ($I-V-T$) and capacitance-voltage-temperature ($C-V-T$) characteristics of molybdenum Schottky contacts on n-InP (100). Journal of Alloys and Compounds, 2009, 485, 467-472.	2.8	73
5	XPS study of sputtered alumina thin films. Ceramics International, 2014, 40, 11099-11107.	2.3	68
6	Effect of annealing on chemical, structural and electrical properties of Au/Gd ₂ O ₃ /n-GaN heterostructure with a high-k rare-earth oxide interlayer. Applied Surface Science, 2018, 427, 670-677.	3.1	68
7	Tetragonal site of transition metal ions doped sodium phosphate glasses. Journal of Alloys and Compounds, 2002, 337, 272-276.	2.8	61
8	Temperature-dependent Schottky barrier parameters of Ni/Au on n-type (001) β -Ga ₂ O ₃ Schottky barrier diode. Vacuum, 2020, 171, 109012.	1.6	60
9	Microstructural, electrical and carrier transport properties of Au/NiO/n-GaN heterojunction with a nickel oxide interlayer. RSC Advances, 2016, 6, 105761-105770.	1.7	58
10	Analysis of the current-voltage characteristics of the Pd/Au Schottky structure on n-type GaN in a wide temperature range. Semiconductor Science and Technology, 2009, 24, 035004.	1.0	52
11	Electrical transport properties of Au/SiO ₂ /n-GaN MIS structure in a wide temperature range. Current Applied Physics, 2012, 12, 765-772.	1.1	43
12	Electrical transport characteristics of Ni/Pd/n-GaN Schottky barrier diodes as a function of temperature. Thin Solid Films, 2011, 519, 3844-3850.	0.8	41
13	Electrical properties of Pt/n-type Ge Schottky contact with PEDOT:PSS interlayer. Journal of Alloys and Compounds, 2013, 549, 18-21.	2.8	40
14	Capacitance-frequency ($C-f$) and conductance-frequency ($G-f$) characteristics of Ir/n-InGaN Schottky diode as a function of temperature. Superlattices and Microstructures, 2013, 60, 358-369.	1.4	40
15	Temperature Dependency And Current Transport Mechanisms Of Pd/V/n-type InP Schottky Rectifiers. Advanced Materials Letters, 2012, 3, 188-196.	0.3	39
16	Current-voltage-temperature ($I-V-T$) characteristics of Pd/Au Schottky contacts on n-InP (111). Current Applied Physics, 2009, 9, 972-977.	1.1	38
17	Effect of annealing on the electronic parameters of Au/poly(ethylmethacrylate)/n-InP Schottky diode with organic interlayer. Current Applied Physics, 2013, 13, 1604-1610.	1.1	38
18	Modified electrical properties and transport mechanism of Ti/p-InP Schottky structure with a polyvinylpyrrolidone (PVP) polymer interlayer. Journal of Materials Science: Materials in Electronics, 2017, 28, 4847-4855.	1.1	37

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19	Analysis of currentâ€“voltageâ€“temperature (â€“â€“) and capacitanceâ€“voltageâ€“temperature (â€“â€“) characteristics of Ni/Au Schottky contacts on n-type InP. Superlattices and Microstructures, 2010, 48, 330-342.	1.4	36
20	Electrical and frequency dependence characteristics of Ti/polyethylene oxide (PEO)/p-type InP organic-inorganic Schottky junction. Journal of Alloys and Compounds, 2017, 695, 2587-2596.	2.8	36
21	Electrical and frequency-dependent properties of Au/Sm2O3/n-GaN MIS junction with a high-k rare-earth Sm2O3 as interlayer. Current Applied Physics, 2017, 17, 980-988.	1.1	35
22	Effect of annealing temperature on electrical properties of Au/polyvinyl alcohol/n-InP Schottky barrier structure. Thin Solid Films, 2012, 520, 5715-5721.	0.8	34
23	Pulsed rf magnetron sputtered alumina thin films. Ceramics International, 2014, 40, 9571-9582.	2.3	32
24	Electrical properties and the double Gaussian distribution of inhomogeneous barrier heights in Se/n-GaN Schottky barrier diode. Superlattices and Microstructures, 2014, 67, 242-255.	1.4	32
25	Electrical Properties of Pt/n-Ge Schottky Contact Modified Using Copper Phthalocyanine (CuPc) Interlayer. Journal of the Electrochemical Society, 2011, 159, H33-H37.	1.3	31
26	Modification of electrical properties of Au/n-type InP Schottky diode with a high-k Ba 0.6 Sr 0.4 TiO 3 interlayer. Superlattices and Microstructures, 2016, 93, 82-91.	1.4	31
27	Barrier Parameters and Current Transport Characteristics of Ti/p-InP Schottky Junction Modified Using Orange G (OG) Organic Interlayer. Journal of Electronic Materials, 2017, 46, 5746-5754.	1.0	30
28	Microstructural, electrical and frequency-dependent properties of Au/p-Cu2ZnSnS4/n-GaN heterojunction. Journal of Colloid and Interface Science, 2017, 499, 180-188.	5.0	30
29	Structural, Chemical and Electrical Properties of Au/La2O3/n-GaN MIS Junction with a High-k Lanthanum Oxide Insulating Layer. Journal of Electronic Materials, 2019, 48, 4217-4225.	1.0	29
30	Analysis of electrical characteristics of Er/p-InP Schottky diode at high temperature range. Current Applied Physics, 2013, 13, 975-980.	1.1	27
31	Effects of high-k zirconium oxide (ZrO2) interlayer on the electrical and transport properties of Au/n-type InP Schottky diode. Thin Solid Films, 2016, 619, 231-238.	0.8	27
32	Electrical and structural properties of Ir/Ru Schottky rectifiers on n-type InGaN at different annealing temperatures. Superlattices and Microstructures, 2013, 56, 64-76.	1.4	26
33	Annealing effects on structural and electrical properties of Ru/Au on n-GaN Schottky contacts. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2007, 137, 200-204.	1.7	25
34	Annealing temperature effect on electrical and structural properties of Cu/Au Schottky contacts to n-type GaN. Microelectronic Engineering, 2008, 85, 470-476.	1.1	25
35	Barrier characteristics of Pt/Ru Schottky contacts on n-type GaN based on Iâ€“Vâ€“T and Câ€“Vâ€“T measurements. Bulletin of Materials Science, 2012, 35, 53-61.	0.8	25
36	Analysis of electrical properties and deep level defects in undoped GaN Schottky barrier diode. Thin Solid Films, 2013, 534, 603-608.	0.8	25

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37	Surface chemical states, electrical and carrier transport properties of Au/ZrO ₂ /n-GaN MIS junction with a high-k ZrO ₂ as an insulating layer. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2018, 231, 74-80.	1.7	25
38	Modification of Schottky Barrier Properties of Ti/p-type InP Schottky Diode by Polyaniline (PANI) Organic Interlayer. <i>Journal of Semiconductor Technology and Science</i> , 2016, 16, 664-674.	0.1	25
39	Electrical properties and conduction mechanism of an organic-modified Au/NiPc/n-InP Schottky barrier diode. <i>Applied Physics A: Materials Science and Processing</i> , 2014, 116, 1379-1387.	1.1	24
40	Rectifying and breakdown voltage enhancement of Au/n-GaN Schottky diode with Al-doped ZnO films and its structural characterization. <i>Thin Solid Films</i> , 2019, 676, 125-132.	0.8	23
41	Electrical characteristics of molybdenum Schottky contacts on n-type GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 112, 30-33.	1.7	22
42	Modified electrical characteristics of Pt/n-type Ge Schottky diode with a pyronine-B interlayer. <i>Superlattices and Microstructures</i> , 2014, 75, 806-817.	1.4	22
43	Temperature Dependent Current-Voltage and Capacitance-Voltage Characteristics of an Au/n-Type Si Schottky Barrier Diode Modified Using a PEDOT:PSS Interlayer. <i>Materials Transactions</i> , 2015, 56, 10-16.	0.4	22
44	Energy-level alignment and electrical properties of Al/p-type Si Schottky diodes with sorbitol-doped PEDOT:PSS as an organic interlayer. <i>Journal of Alloys and Compounds</i> , 2015, 637, 84-89.	2.8	22
45	Electrical and interfacial properties of Au/n-InP Schottky contacts with nickel phthalocyanine (NiPc) interlayer. <i>Indian Journal of Physics</i> , 2015, 89, 463-469.	0.9	21
46	Double Gaussian Distribution of Barrier Heights, Interface States, and Current Transport Mechanisms in Au/Bi _{0.5} Na _{0.5} TiO ₃ -BaTiO ₃ /n-GaN MIS Structure. <i>Journal of Electronic Materials</i> , 2015, 44, 549-557.	1.0	21
47	Electrical properties and interfacial reactions of rapidly annealed Ni/Ru Schottky rectifiers on n-type GaN. <i>Journal of Alloys and Compounds</i> , 2010, 503, 186-191.	2.8	20
48	Optical and Microstructural Characterisations of Pulsed rf Magnetron Sputtered Alumina Thin Film. <i>Journal of Materials Science and Technology</i> , 2013, 29, 929-936.	5.6	20
49	Microstructural, chemical states and electrical properties of Au/CuO/n-InP heterojunction with a cupric oxide interlayer. <i>Vacuum</i> , 2018, 152, 15-24.	1.6	20
50	Studies on zirconium nitride films deposited by reactive magnetron sputtering. <i>Crystal Research and Technology</i> , 2003, 38, 1047-1051.	0.6	19
51	Effects of thermal annealing on the electrical and structural properties of Pt/Mo Schottky contacts on n-type GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2009, 20, 1018-1025.	1.1	19
52	Electrical properties and the role of inhomogeneities at the polyvinyl alcohol/n-InP schottky barrier interface. <i>Journal of Applied Polymer Science</i> , 2014, 131, .	1.3	19
53	Electrical parameters and series resistance analysis of Au/Y/p-InP/Pt Schottky barrier diode at room temperature. <i>AIP Conference Proceedings</i> , 2016, , .	0.3	19
54	Electrical and carrier transport properties of the Au/Y ₂ O ₃ /n-GaN metal-insulator-semiconductor (MIS) diode with rare-earth oxide interlayer. <i>Applied Physics A: Materials Science and Processing</i> , 2017, 123, 1.	1.1	19

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55	Temperature-Dependent Current–Voltage (I – V) and Capacitance–Voltage (C – V) Characteristics of Ni/Cu/n-InP Schottky Barrier Diodes. Brazilian Journal of Physics, 2013, 43, 13-21.	0.7	18
56	Electrical properties of Au/Bi _{0.5} Na _{0.5} TiO ₃ -BaTiO ₃ /n-GaN metal–insulator–semiconductor (MIS) structure. Semiconductor Science and Technology, 2014, 29, 075001.	1.0	18
57	Double Gaussian barrier distribution of permalloy (Ni _{0.8} Fe _{0.2}) Schottky contacts to n-type GaN. Superlattices and Microstructures, 2018, 120, 508-516.	1.4	18
58	Electrical Properties and Interface States of Rare-Earth Metal Ytterbium Schottky Contacts to p-Type InP. Materials Transactions, 2013, 54, 2173-2179.	0.4	17
59	Effect of annealing temperature on the electrical and structural properties of V/p-GaN Schottky structures. Thin Solid Films, 2016, 598, 236-242.	0.8	17
60	Microstructural, chemical and electrical characteristics of Au/magnetite (Fe ₃ O ₄)/n-GaN MIS junction with a magnetite interlayer. Vacuum, 2019, 164, 233-241.	1.6	17
61	Effect of annealing temperature on electrical and structural properties of transparent indium tin oxide electrode to n-type GaN. Materials Chemistry and Physics, 2009, 114, 821-826.	2.0	16
62	Evaluation of Schottky barrier parameters of Pd/Pt Schottky contacts on n-InP (100) in wide temperature range. Superlattices and Microstructures, 2009, 45, 22-32.	1.4	16
63	Potato Chip-Like OD Interconnected ZnCo ₂ O ₄ Nanoparticles for High-Performance Supercapacitors. Crystals, 2021, 11, 469.	1.0	16
64	Structural and electrical properties of Mo/n-GaN Schottky diodes. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 622-627.	0.8	15
65	Influence of rapid thermal annealing effect on electrical and structural properties of Pd/Ru Schottky contacts to n-type GaN. Materials Chemistry and Physics, 2011, 130, 1000-1006.	2.0	15
66	Development of SiO ₂ based thin film on metal foils for space application. Ceramics International, 2013, 39, 8493-8498.	2.3	15
67	Effect of annealing temperature on the electrical properties of Au/Ta ₂ O ₅ /n-GaN metal–insulator–semiconductor (MIS) structure. Applied Physics A: Materials Science and Processing, 2013, 113, 713-722.	1.1	15
68	Electrical properties of Ir/n-InGaN/Ti/Al Schottky barrier diode in a wide temperature range. Advanced Materials Letters, 2014, 5, 31-38.	0.3	15
69	Annealing effects on zirconium nitride films. Applied Surface Science, 2004, 230, 88-93.	3.1	14
70	Influence of nanostructure Fe-doped ZnO interlayer on the electrical properties of Au/n-type InP Schottky structure. Materials Chemistry and Physics, 2016, 177, 92-98.	2.0	14
71	Temperature-Dependent Electrical Properties and Carrier Transport Mechanisms of TMAH-Treated Ni/Au/Al ₂ O ₃ /GaN MIS Diode. Journal of Electronic Materials, 2016, 45, 5655-5662.	1.0	14
72	Effect of seed layers (Al, Ti) on optical and morphology of Fe-doped ZnO thin film nanowires grown on Si substrate via electron beam evaporation. Materials Science in Semiconductor Processing, 2017, 71, 296-303.	1.9	14

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73	Microstructural and electrical properties of Al/n-type Si Schottky diodes with Au-CuPc nanocomposite films as interlayer. Superlattices and Microstructures, 2017, 111, 506-517.	1.4	14
74	Effect of copper phthalocyanine thickness on surface morphology, optical and electrical properties of Au/CuPc/n-Si heterojunction. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	1.1	14
75	Effect of rapid thermal annealing on deep level defects in the Si-doped GaN. Microelectronic Engineering, 2010, 87, 117-121.	1.1	13
76	Electrical and structural properties of rapidly annealed rare-earth metal Er Schottky contacts on p-type InP. Superlattices and Microstructures, 2014, 65, 206-218.	1.4	13
77	Electrical Properties and Carrier Transport Mechanism of Au<i>and n</i>-GaN Schottky Contact Modified Using a Copper Pthalocyanine (CuPc) Interlayer. Materials Transactions, 2014, 55, 758-762.	0.4	13
78	Annealing effects on the electrical, structural and morphological properties of Ti/p-GaN/Ni/Au Schottky diode. Applied Physics A: Materials Science and Processing, 2015, 121, 131-140.	1.1	13
79	Influence of rapid thermal annealing on electrical and structural properties of double metal structure Au/Ni/n-InP (111) diodes. Current Applied Physics, 2010, 10, 687-692.	1.1	12
80	Influence of Annealing on Electrical Properties of an Organic Thin Layer-Based n-Type InP Schottky Barrier Diode. Journal of Electronic Materials, 2013, 42, 1282-1289.	1.0	12
81	Electronic parameters and carrier transport mechanism of high-barrier Se Schottky contacts to n-type GaN. Solid State Communications, 2014, 179, 34-38.	0.9	12
82	Rapid thermal annealing effects on the electrical, structural and morphological properties of Yb/p-type InP Schottky Structure. Electronic Materials Letters, 2015, 11, 73-81.	1.0	12
83	Schottky Barrier Parameters and Low-Frequency Noise Characteristics of Au/Ni Contact to n-Type $\text{In}^{2-}\text{Ga}_2\text{O}_3$. Journal of Electronic Materials, 2020, 49, 297-305.	1.0	12
84	Electrical and carrier transport properties of Au/Pr6O11/n-GaN MIS structure with a high-k rare-earth oxide interlayer at high temperature range. Vacuum, 2020, 174, 109201.	1.6	12
85	Electrical properties of thermally stable Pt/Re/Au ohmic contacts to p-type GaN. Solid-State Electronics, 2004, 48, 1563-1568.	0.8	11
86	Electrical and structural properties of low-resistance Pt/Ag/Au ohmic contacts to p-type GaN. Solid-State Electronics, 2005, 49, 1213-1216.	0.8	11
87	Study of the electrical, structural and surface morphological characteristics of Pt/Re/Au ohmic contacts on p-type GaN. Materials Chemistry and Physics, 2005, 93, 286-290.	2.0	11
88	Current transport mechanisms in Ru/Pd/n-GaN Schottky barrier diodes and deep level defect studies. Superlattices and Microstructures, 2012, 52, 484-499.	1.4	11
89	Effect of annealing on the electrical and interface properties of Au/PVC/n-InP organic-on-inorganic structures. Microelectronic Engineering, 2014, 114, 31-37.	1.1	11
90	Influence of tetramethylammonium hydroxide treatment on the electrical characteristics of Ni/Au/GaN Schottky barrier diode. Materials Chemistry and Physics, 2014, 143, 801-805.	2.0	11

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91	Effect of rare-earth Pr6O11 insulating layer on the electrical properties of Au/n-GaN Schottky electrode and its chemical and structural characterization. Journal of Materials Science: Materials in Electronics, 2019, 30, 18710-18719.	1.1	11
92	Annealing Effects on Electrical Properties and Interfacial Reactions of Ni/Cu Schottky Rectifiers on n-Type InP. Journal of Modern Physics, 2012, 03, 538-545.	0.3	11
93	The effect of annealing temperature on electrical and structural properties of Rh/Au Schottky contacts to n-type GaN. Semiconductor Science and Technology, 2006, 21, 1753-1757.	1.0	10
94	Rapid thermal annealing effects on electrical and structural properties of Pd/Au Schottky contacts to n-type InP(111). Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 250-255.	0.8	10
95	Electrical Properties of Rapidly Annealed Ir and Ir/Au Schottky Contacts on n-Type InGaIn. Journal of Metallurgy, 2012, 2012, 1-9.	1.1	10
96	Influence of annealing temperature on the electrical and structural properties of palladium Schottky contacts on n-type 4H-SiC. Superlattices and Microstructures, 2014, 76, 55-65.	1.4	10
97	Effect of thermal annealing on the electrical and structural properties of Au/Y/p-type InP Schottky structure. Vacuum, 2015, 119, 276-283.	1.6	10
98	Effect of copper phthalocyanine (CuPc) interlayer on the electrical characteristics of Au/n-GaN Schottky rectifier. Materials Science in Semiconductor Processing, 2015, 30, 420-428.	1.9	10
99	Temperature dependent Schottky barrier characteristics of Al/n-type Si Schottky barrier diode with Au-Cu phthalocyanine interlayer. Thin Solid Films, 2020, 713, 138343.	0.8	10
100	Influence of tin oxide (SnO2) interlayer on the electrical and reverse current conduction mechanism of Au/n-InP Schottky junction and its microstructural properties. Thin Solid Films, 2021, 740, 139001.	0.8	10
101	Electrical and structural properties of double metal structure Ni/V Schottky contacts on n-InP after rapid thermal process. Journal of Materials Science, 2011, 46, 558-565.	1.7	9
102	SYNTHESIS AND CHARACTERIZATION OF NICKEL DOPED CdS NANOPARTICLES. International Journal of Nanoscience, 2012, 11, 1240006.	0.4	9
103	Depinning of the Fermi level at the Ge Schottky interface through Se treatment. Scripta Materialia, 2013, 69, 809-811.	2.6	9
104	Electrical properties and carrier transport mechanism in V/p-GaN Schottky diode at high temperature range. Superlattices and Microstructures, 2015, 86, 157-165.	1.4	9
105	Influence of rapid thermal annealing on electrical and structural properties of Pd/Au Schottky contact to Ga-polarity GaN grown on Si (111) substrate. Journal of Alloys and Compounds, 2017, 705, 782-787.	2.8	9
106	Microstructural and interface properties of Au/SrTiO3 (STO)/n-GaN heterojunction with an e-beam evaporated high-k STO interlayer. Journal of Alloys and Compounds, 2020, 823, 153775.	2.8	9
107	Electrical and carrier transport properties of TiO2/p-InP MPS junction with a TiO2 polymer interlayer. Journal of Materials Science: Materials in Electronics, 2021, 32, 8092-8105.	1.1	9
108	Influence of Series Resistance and Interface State Density on Electrical Characteristics of Ru/Ni/n-GaN Schottky structure. Journal of Semiconductor Technology and Science, 2013, 13, 492-499.	0.1	9

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109	Effects of Rapid Thermal Annealing on the Structural, Optical, and Electrical Properties of Au/CuPc/n-Si (MPS)-type Schottky Barrier Diodes. <i>Applied Physics A: Materials Science and Processing</i> , 2021, 127, 1.	1.1	9
110	Electrical and structural properties of Ti/W/Au ohmic contacts on n-type GaN. <i>Semiconductor Science and Technology</i> , 2004, 19, 975-979.	1.0	8
111	Thermal annealing behaviour on Schottky barrier parameters and structural properties of Au contacts to n-type GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 333-338.	1.1	8
112	Effect of rapid thermal annealing on the electrical and structural properties of Ru/n-InP (100) Schottky rectifiers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2658-2664.	0.8	8
113	Effects of annealing temperature on electrical and structural properties of Mo/n-InP (100) Schottky contacts. <i>Surface and Interface Analysis</i> , 2009, 41, 905-910.	0.8	8
114	Structural and electrical properties of rapidly annealed Ni/Mo Schottky barriers on n-type GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 753-759.	0.8	8
115	Electrical characteristics and interfacial reactions of rapidly annealed Pt/Ru Schottky contacts on n-type GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 1670-1677.	0.8	8
116	Electrical and interface properties of PdAl/Au metal alloyed ohmic contacts on p-type GaN for high-temperature MEMS devices. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 16903-16909.	1.1	8
117	Effect of annealing temperature on electrical characteristics of ruthenium-based Schottky contacts on n-type GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2006, 17, 999-1004.	1.1	7
118	Electrical and structural properties of rapidly annealed Pd/Mo Schottky contacts on n-type GaN. <i>Semiconductor Science and Technology</i> , 2008, 23, 095026.	1.0	7
119	Analysis of temperature-dependent Schottky barrier parameters of Cu-Au Schottky contacts to n-InP. <i>Canadian Journal of Physics</i> , 2012, 90, 73-81.	0.4	7
120	Electrical transport properties of Ru/Cu/n-InP Schottky barrier diode based on temperature-dependent I-V and C-V measurements. <i>Indian Journal of Physics</i> , 2012, 86, 687-695.	0.9	7
121	Electrical and structural properties of tungsten Schottky contacts to p-type InP at different annealing temperatures. <i>Superlattices and Microstructures</i> , 2014, 71, 134-146.	1.4	7
122	Temperature-dependent electrical parameters and current transport mechanisms of Ru/Ti/n-InP Schottky diodes. <i>Indian Journal of Physics</i> , 2015, 89, 1161-1168.	0.9	7
123	Effect of annealing temperature on the electrical, structural and surface morphological properties of Ru/Ti Schottky contacts on n-type InP. <i>Superlattices and Microstructures</i> , 2015, 86, 280-291.	1.4	7
124	Transport mechanisms and interface properties of W/p-InP Schottky diode at room temperature. <i>Indian Journal of Physics</i> , 2016, 90, 399-406.	0.9	7
125	Microstructural properties of thermally stable Ti/W/Au ohmic contacts on n-type GaN. <i>Microelectronic Engineering</i> , 2006, 83, 1981-1985.	1.1	6
126	The influence of rapid thermal annealing on electrical and structural properties of Pt/Au Schottky contacts to n-type InP. <i>Journal of Materials Science: Materials in Electronics</i> , 2010, 21, 804-810.	1.1	6

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127	Structural, electrical, and surface morphological characteristics of rapidly annealed Pt/Ti Schottky contacts to n-type InP. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 2406-2414.	0.8	6
128	Electrical properties and transport mechanisms of Au/Ba _{0.6} Sr _{0.4} TiO ₃ /GaN metal-insulator-semiconductor (MIS) diode at high temperature range. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	6
129	Effect of Temperature on the Electrical and Current Transport Properties of Au/Nd ₂ O ₃ /n-GaN Metal/Interlayer/Semiconductor (MIS) Junction. <i>Applied Physics A: Materials Science and Processing</i> , 2021, 127, 1.	1.1	6
130	Low-resistance and thermally stable Pd/Re ohmic contacts to p-type GaN. <i>Semiconductor Science and Technology</i> , 2003, 18, 541-544.	1.0	5
131	Electrical characteristics of ZrN metallised metal-oxide-semiconductor and metal-insulator-metal devices. <i>Journal of Materials Science: Materials in Electronics</i> , 2006, 17, 335-339.	1.1	5
132	Microstructural and electrical characteristics of rapidly annealed Ni/Mo Schottky rectifiers on cleaned n-type GaN (0001) surface. <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 286-291.	1.1	5
133	Electrical, structural and morphological characteristics of rapidly annealed Pd/n-InP (100) Schottky structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 854-861.	1.1	5
134	Electrical and structural properties of Pd/n-type InP (111) Schottky structure as a function of annealing temperature. <i>Surface and Interface Analysis</i> , 2012, 44, 98-104.	0.8	5
135	Effect of Rapid Thermal Annealing on the Electrical and Structural Properties of Se Schottky Contacts to n-Type Si. <i>Materials Transactions</i> , 2013, 54, 1067-1072.	0.4	5
136	CdS microflowers and interpenetrated nanorods grown on Si substrate: Structural, optical properties and growth mechanism. <i>Materials Chemistry and Physics</i> , 2014, 146, 399-405.	2.0	5
137	Ru/Ti Schottky Contacts on N-type In-P (100): Temperature Dependence of Current-Voltage (I-V) Characteristics. , 2015, 10, 666-672.		5
138	Rapid thermal annealing effects on the electrical and structural properties of Ru/V/n-InP Schottky barrier diode. <i>Superlattices and Microstructures</i> , 2015, 83, 48-60.	1.4	5
139	Modification of Schottky barrier properties of Al/p-type Si Schottky rectifiers with graphene-oxide-doped poly(3,4-ethylenedioxythiophene):poly(styrene sulfonate) interlayer. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	5
140	Electrical transport and current properties of rare-earth dysprosium Schottky electrode on p-type GaN at various annealing temperatures. <i>Journal of Semiconductors</i> , 2017, 38, 114001.	2.0	5
141	Barrier enhancement of Al/n-InP Schottky diodes by graphene oxide thin layer. <i>Indian Journal of Physics</i> , 2019, 93, 467-474.	0.9	5
142	Thermal stability of high-k Er-silicate gate dielectric formed by interfacial reaction between Er and SiO ₂ films. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 122-125.	1.9	4
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